

VX-2 Series Power MOSFET

N-Channel Enhancement type

2SK2180

(F3V50VX2)

500V3A

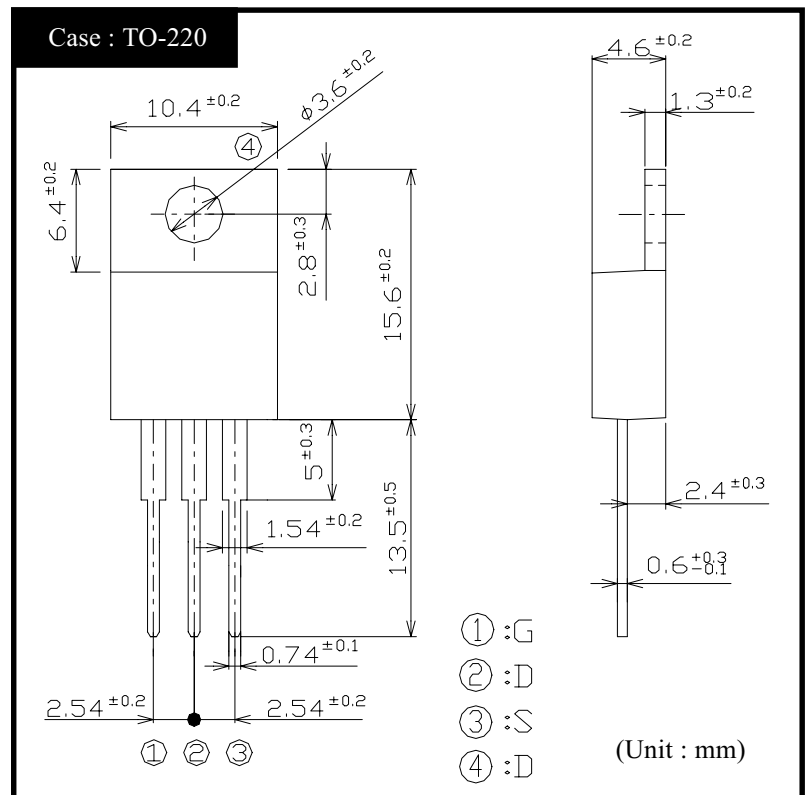
FEATURES

- Input capacitance (C_{iss}) is small.
Especially, input capacitance at 0 bias is small.
- The static $R_{ds(on)}$ is small.
- The switching time is fast.

APPLICATION

- Switching power supply of AC 100V input
- High voltage power supply
- Inverter

OUTLINE DIMENSIONS



RATINGS

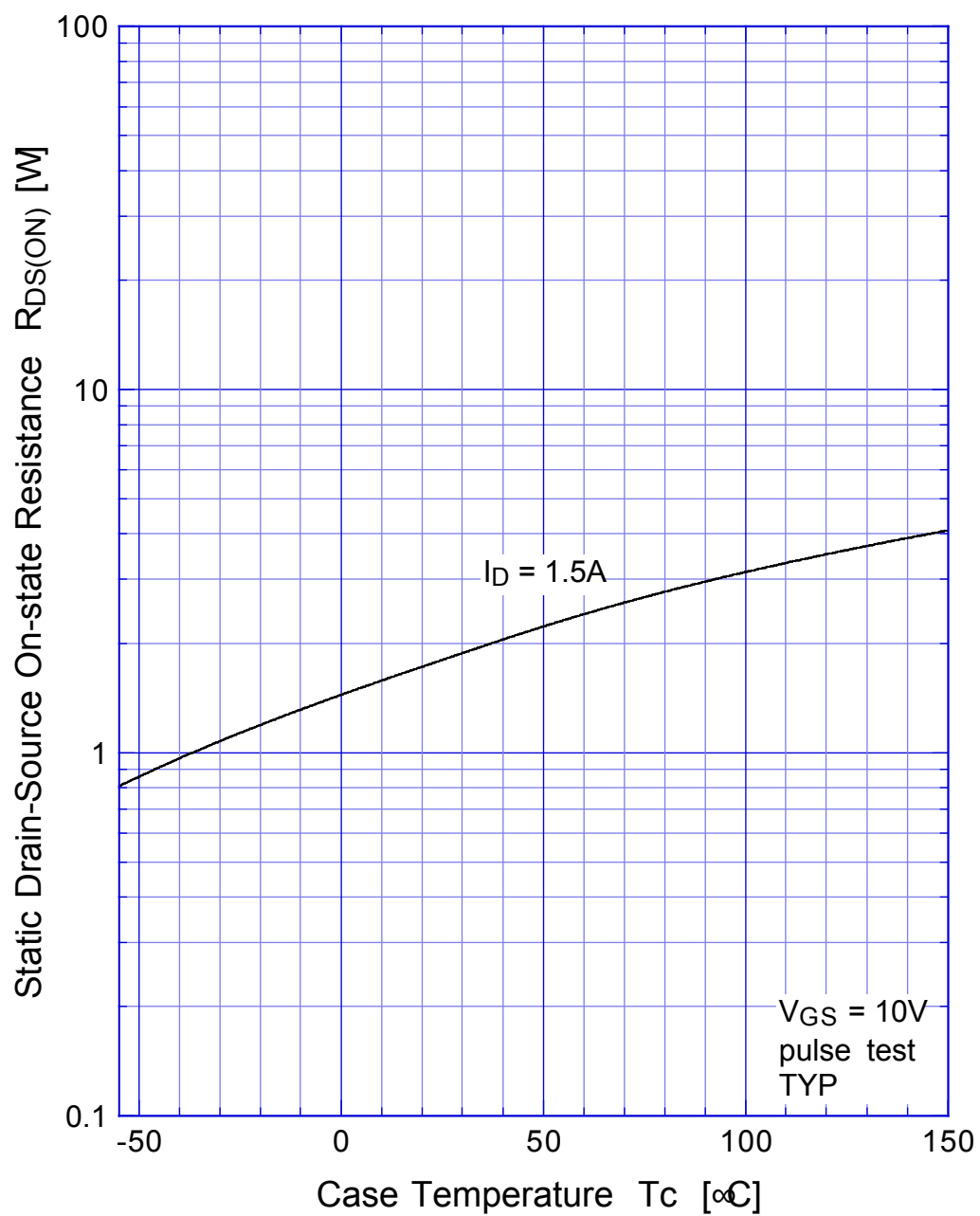
- Absolute Maximum Ratings (Tc = 25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T _{stg}		-55~150	°C
Channel Temperature	T _{ch}		150	
Drain-Source Voltage	V _{DSS}		500	V
Gate-Source Voltage	V _{GSS}		±30	
Continuous Drain Current(DC)	I _D		3	A
Continuous Drain Current(Peak)	I _{DP}		9	
Continuous Source Current(DC)	I _S		3	
Total Power Dissipation	P _T		40	W
Single Pulse Avalanche Current	I _{AS}	T _{ch} = 25°C	3	A
Mounting Torque	TOR	(Recommended torque : 0.3 N・m)	0.5	N・m

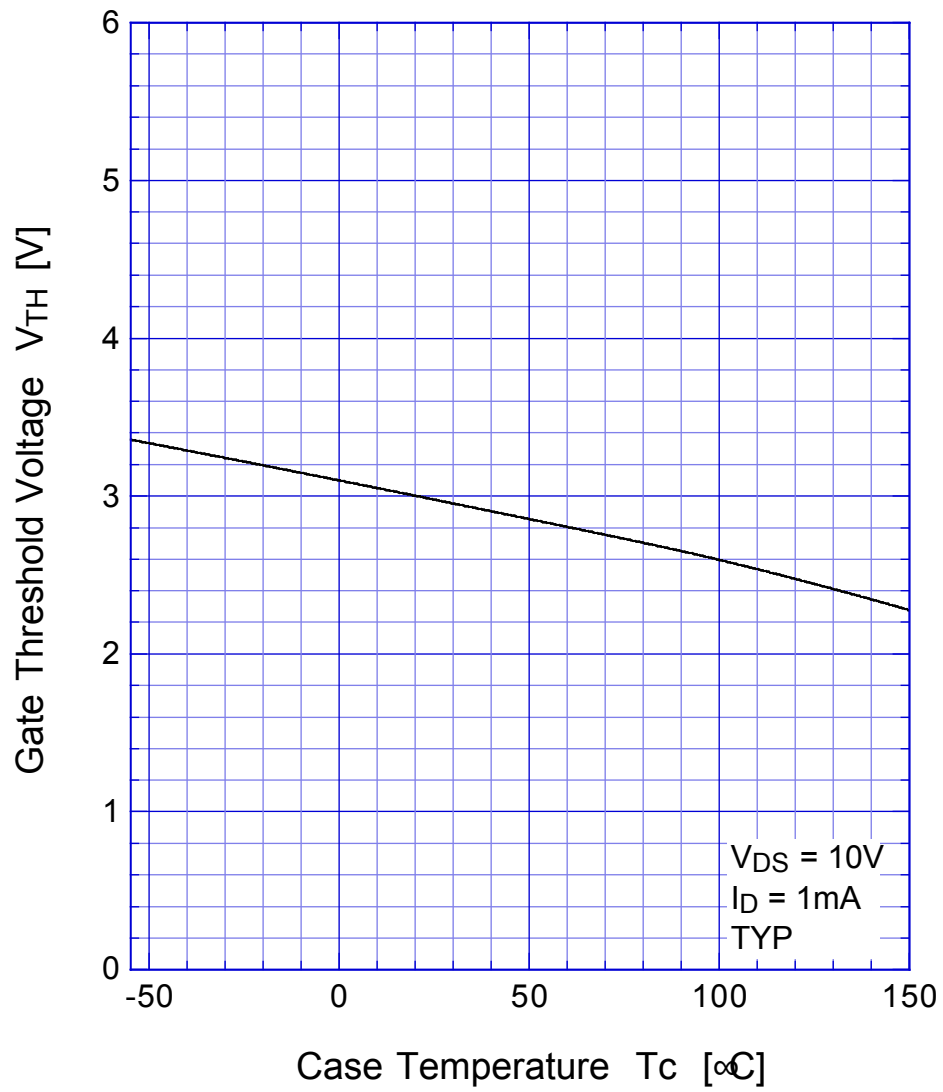
●Electrical Characteristics $T_c = 25^{\circ}\text{C}$

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}$, $V_{GS} = 0\text{V}$	500			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500\text{V}$, $V_{GS} = 0\text{V}$			250	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$			± 0.1	
Forward Transconductance	g_{fs}	$I_D = 1.5\text{A}$, $V_{DS} = 10\text{V}$	0.9	2.1		S
Static Drain-Source On-state Resistance	$R_{DS(ON)}$	$I_D = 1.5\text{A}$, $V_{GS} = 10\text{V}$		1.8	2.3	Ω
Gate Threshold Voltage	V_{TH}	$I_D = 0.3\text{mA}$, $V_{DS} = 10\text{V}$	2.5	3.0	3.5	V
Source-Drain Diode Forwade Voltage	V_{SD}	$I_S = 1.5\text{A}$, $V_{GS} = 0\text{V}$			1.5	
Thermal Resistance	θ_{jc}	junction to case			3.12	$^{\circ}\text{C}/\text{W}$
Total Gate Charge	Q_g	$V_{DD} = 400\text{V}$, $V_{GS} = 10\text{V}$, $I_D = 3\text{A}$		15		nC
Input Capacitance	C_{iss}	$V_{DS} = 10\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		400		pF
Reverse Transfer Capacitance	C_{rss}			30		
Output Capacitance	C_{oss}			90		
Turn-On Time	t_{on}	$I_D = 1.5\text{A}$, $V_{GS} = 10\text{V}$, $R_L = 100\Omega$		45	80	ns
Turn-Off Time	t_{off}			90	140	

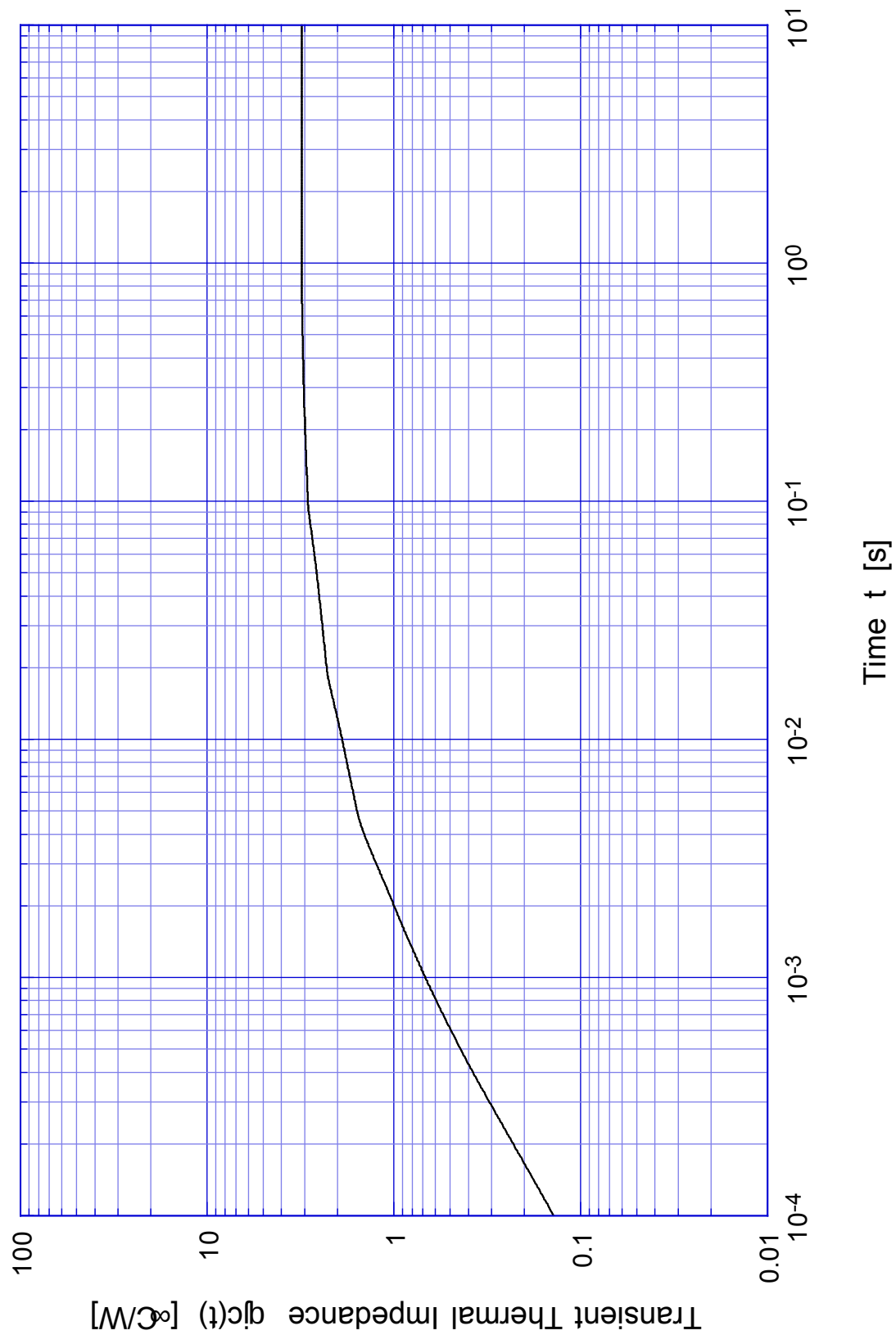
2SK2180 Static Drain-Source On-state Resistance



2SK2180 Gate Threshold Voltage



2SK2180 Transient Thermal Impedance



2SK2180

Power Derating

